

ADVANCED ELECTRONIC MATERIALS

Supporting Information

for *Adv. Electron. Mater.*, DOI: 10.1002/aelm.201700414

Zone-Annealing-Assisted Solvent-Free Processing of
Complementary Semiconducting Polymer Blends for Organic
Field-Effect Transistors

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Supporting figures and captions

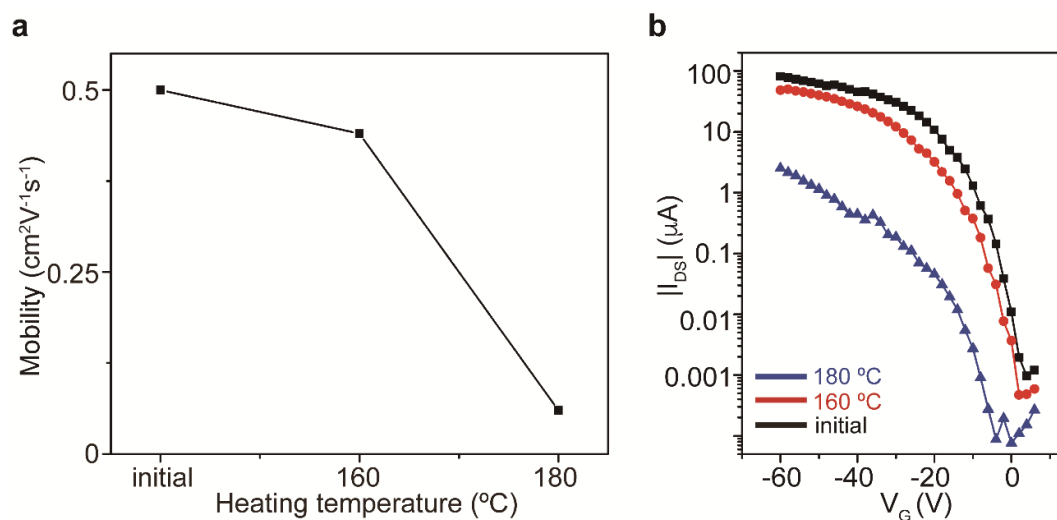


Figure S1. FET characteristics of the *c*-SPB film annealed by uniform heating in air. (a) Mobility trend of FETs comparing the drop-casted film with the uniform annealed film at different temperatures. The initial represented the film processed from drop casting. (b) Transfers of a typical device at the three conditions.

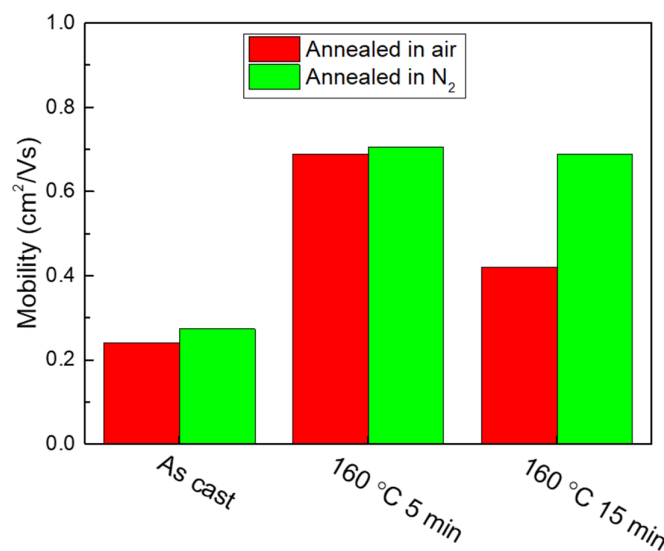


Figure S2. Mobility of the *c*-SPB film annealed by uniform heating in air and in N₂ glovebox as different conditions. For the film annealed in air, the mobility could be improved by annealing for 5 min, but dramatically decreased by annealing for 15 min, illustrating the disadvantage of uniform heating. For the film annealed in N₂, the mobility was improved and shown little difference at different annealing time. However, the results were not as good as those from zone annealing method in air. The data here were based on 10 devices.

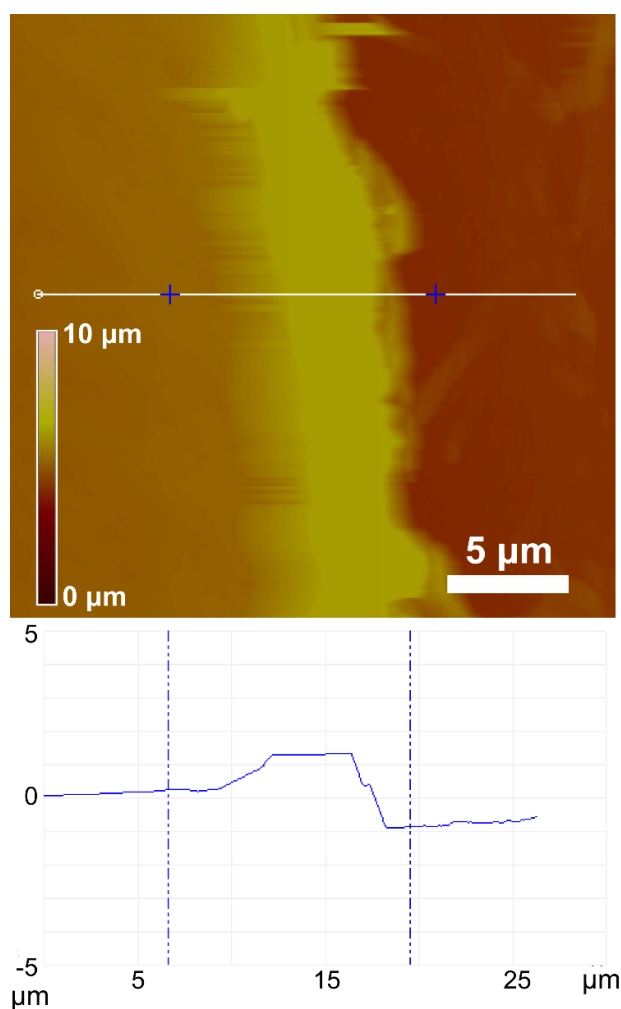


Figure S3. Thickness of hot pressed c-SPB thin film measured by atomic force microscopy.

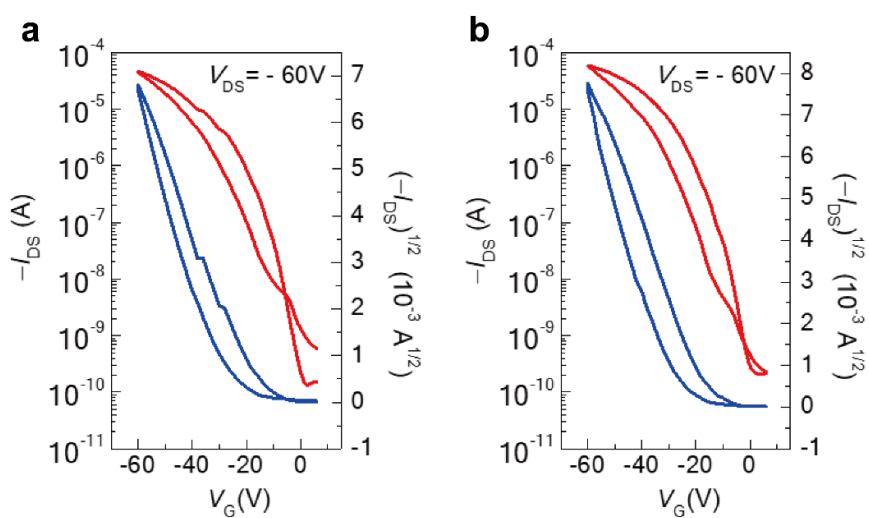


Figure S4. Hysteresis characteristics of the c-SPB film annealed by uniform heating in air (a) and zone annealing in ambient (b).